

**SEMICONDUCTOR DEVICE HAVING HIGH DRIVE CURRENT
AND METHOD OF MANUFACTURE THEREFOR**

ABSTRACT

[0035] A semiconductor device including an isolation region located in a substrate, an NMOS device located partially over a surface of the substrate, and a PMOS device isolated from the NMOS device by the isolation region and located partially over the surface. A first one of the NMOS and PMOS devices includes one of: (1) first source/drain regions recessed within the surface; and (2) first source/drain regions extending from the surface. A second one of the NMOS and PMOS devices includes one of: (1) second source/drain regions recessed within the surface wherein the first source/drain regions extend from the surface; (2) second source/drain regions extending from the surface wherein the first source/drain regions are recessed within the surface; and (3) second source/drain regions substantially coplanar with the surface.